



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _C = +25°C
60)/	7.5 m Ω @ V _{GS} = 10V	60A
60V	11.5m Ω @ V _{GS} = 4.5V	49A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

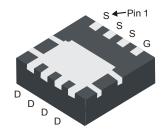
Features and Benefits

- Low R_{DS(ON)} Ensures on State Losses Are Minimized
- Excellent Q_{gd} x R_{DS (ON)} Product (FOM)
- Advanced Technology for DC/DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) rated
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

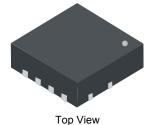
Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (approximate)

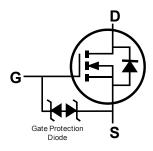




Bottom View



Internal Schematic



Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6008LFG-7	POWERDI3333-8	2,000/Tape & Reel
DMT6008LFG-13	POWERDI3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



S6E = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 13 = 2013) WW = Week code (01 ~ 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	60	V
Gate-Source Voltage		V _{GSS}	±12	V
Continuous Drain Current (Note EVV - 40V	T _A = +25°C T _A = +70°C	I _D	13 11	А
Continuous Drain Current (Note 5) V _{GS} = 10V	T _C = +25°C T _C = +70°C	I _D	60 48	А
Maximum Continuous Body Diode Forward Current (Note 5)	I _S	3	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	80	Α	
Avalanche Current (Note 6)		I _{AS}	13	Α
Avalanche Energy (Note 6)	E _{AS}	25	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

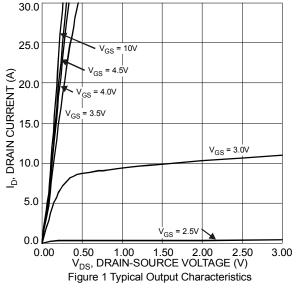
Characteristic	Symbol	Value	Units		
Total Power Dissipation (Note 5)	T _A = +25°C	D-	2.2	W	
Total Fower Dissipation (Note 3)	T _C = +25°C	P_D	41		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	П	58		
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	35	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	3			
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C		

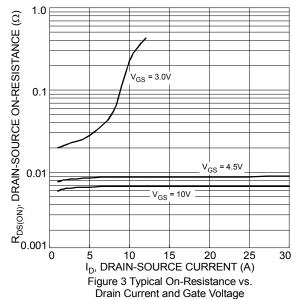
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

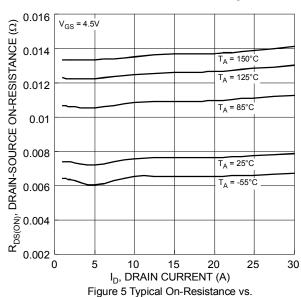
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.7		2.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
	R _{DS(ON)}	_	5.0	7.5	mΩ	$V_{GS} = 10V, I_D = 20A$
Static Drain-Source On-Resistance		_	6.5	11.5		$V_{GS} = 4.5V, I_D = 20A$
		_	19	_		$V_{GS} = 3V, I_D = 3A$
Diode Forward Voltage	V_{SD}	_	0.9	1.2	V	V _{GS} = 0V, I _S = 20A
DYNAMIC CHARACTERISTICS (Note 8)				•		
Input Capacitance	C _{iss}	_	2713	_		V _{DS} = 30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	822	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	57	_		
Gate Resistance	Rg	_	0.54	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	22.4	_		V _{DS} = 30V, I _D = 20A
Total Gate Charge (V _{GS} = 10V)	Qg	_	50.4	_	nC	
Gate-Source Charge	Qgs	_	9.6	_	IIC	
Gate-Drain Charge	Q_{gd}	_	7.8	_		
Turn-On Delay Time	t _{D(on)}		7.0	_		V _{DD} = 30V, V _{GS} = 10V,
Turn-On Rise Time	t _r	_	4.4	_	nS	
Turn-Off Delay Time	t _{D(off)}	_	24.4	_	113	$I_D = 20A$, $R_G = 3\Omega$,
Turn-Off Fall Time	t _f		7.0			

^{5.} R_{OJA} is determined with the device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. R_{BJC} is guaranteed by design S. R_{OJA} is determined with the device informed on Fr.4 substrate while R_{OJA} is determined by the user's board design.
6. UIS in production with L = 0.3mH, T_J = +25°C
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

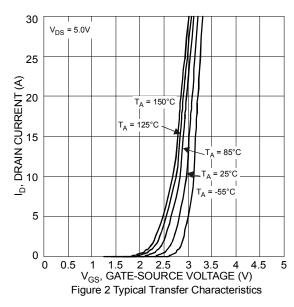


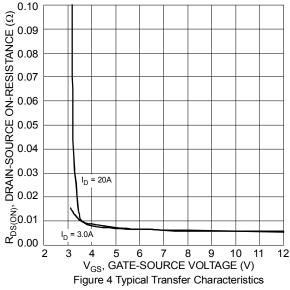


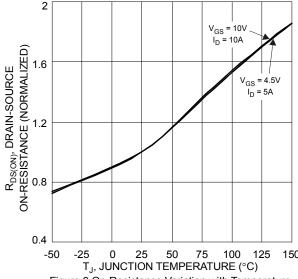




Drain Current and Temperature









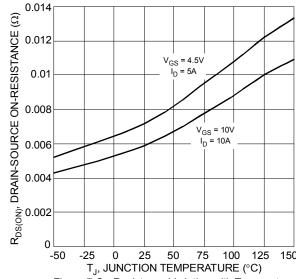


Figure 7 On-Resistance Variation with Temperature

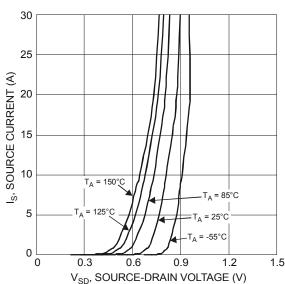


Figure 9 Diode Forward Voltage vs. Current

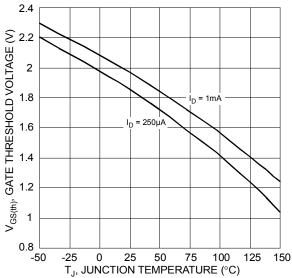
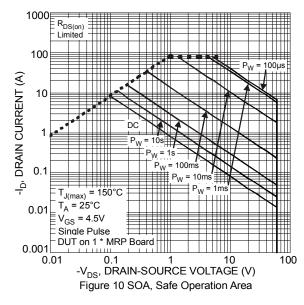
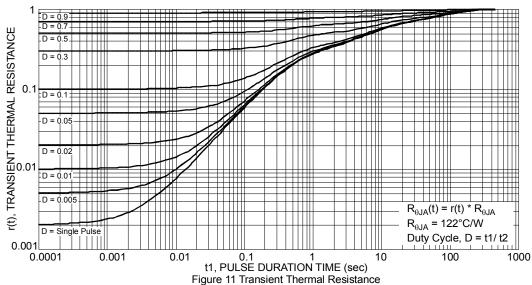


Figure 8 Gate Threshold Variation vs. Ambient Temperature

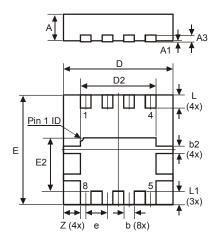






Package Outline Dimensions

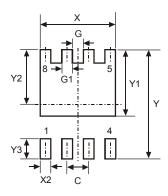
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Р	POWERDI [®] 3333-8					
Dim	Min	Max	Тур			
D	3.25	3.35	3.30			
Е	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
E2	1.56	1.66	1.61			
Α	0.75	0.85	0.80			
A1	0	0.05	0.02			
A3	-	-	0.203			
b	0.27	0.37	0.32			
b2	_	_	0.20			
L	0.35	0.45	0.40			
L1	_	_	0.39			
е	_	_	0.65			
Z	_	_	0.515			
All I	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	0.650		
G	0.230		
G1	0.420		
Y	3.700		
Y1	2.250		
Y2	1.850		
Y3	0.700		
Х	2.370		
¥2	0.420		



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